



SB3060LCT

DUAL HIGH-VOLTAGE SCHOTTKY RECTIFIER

VOLTAGE 60 Volts **CURRENT** 30 Amperes

FEATURES

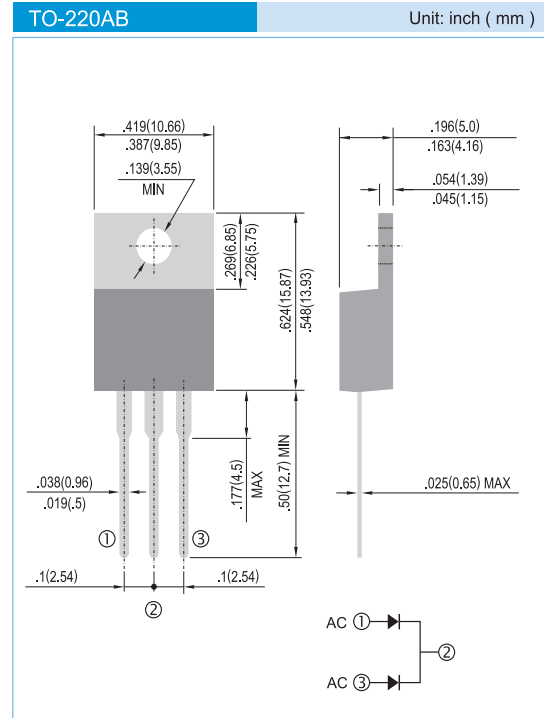
- Low forward voltage drop, low power losses
- High efficiency operation
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

Case : TO-220AB, Plastic

Terminals : Solderable per MIL-STD-750, Method 2026

Weight: 0.0655 ounces, 1.859 grams



MAXIMUM RATINGS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	60	V
Maximum average forward rectified current (Fig.1)	$I_{F(AV)}$	30 15	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	I_{FSM}	250	A
Non-repetitive avalanche energy at $T_J=25^{\circ}\text{C}$, $L=60\text{mH}$ per diode	E_{AS}	450	mJ
Typical Thermal Resistance	$R_{\theta JC}$	2.5	$^{\circ}\text{C}/\text{W}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to + 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	V_{BR}	$I_R=1\text{mA}$	60	-	-	V
Instantaneous forward voltage per diode ⁽¹⁾	V_F	$I_F=15\text{A}$ $I_F=30\text{A}$	-	-	0.60 0.75	V
		$I_F=15\text{A}$ $I_F=30\text{A}$	-	0.48 0.64	0.56 0.70	V
Reverse current per diode ⁽¹⁾	I_R	$V_R=60\text{V}$	-	-	480	μA
			-	-	150	mA

Note.1 Pulse test : $t_p=380\mu\text{s}$, $\delta<2\%$

PAN JIT RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE



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RATINGS AND CHARACTERISTICS CURVES ($T_A=25^\circ\text{C}$ unless otherwise noted)

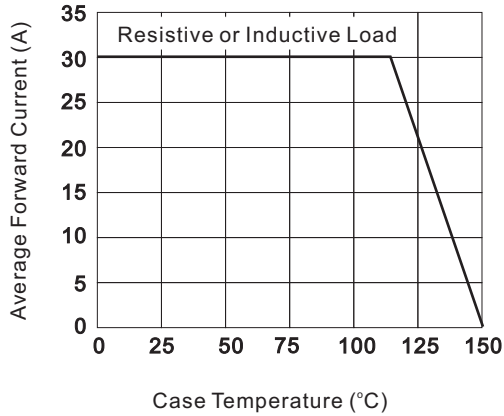


Figure 1. Forward Current Derating Curve

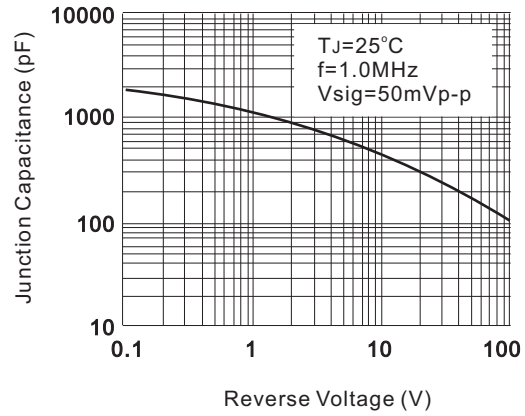


Figure 2. Typical Junction Capacitance

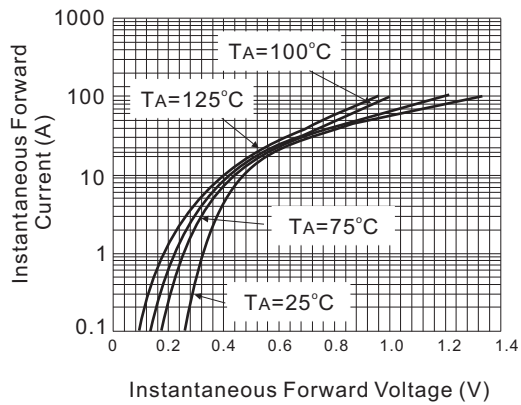


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

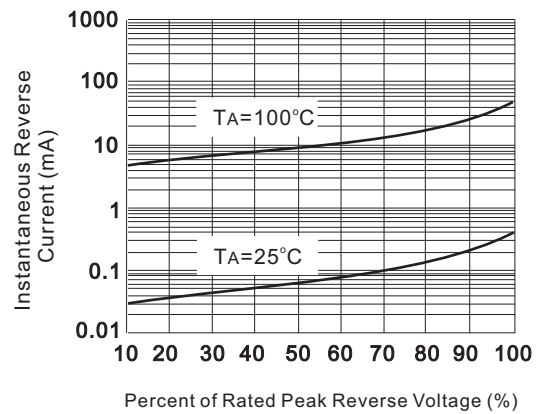


Figure 4. Typical Reverse Characteristics Per Diode